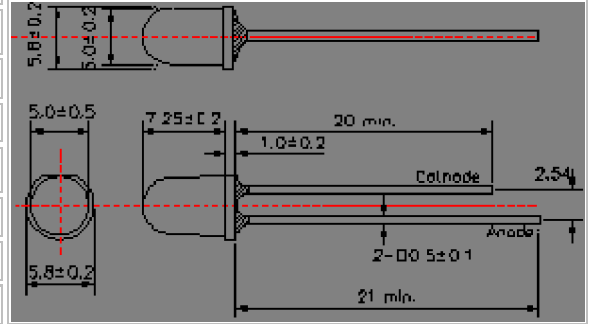


LED1050-03 Infrared LED Lamp

LED1050-03US is an GaAs LED mounted on a lead frame with a clear epoxy lens.
On forward bias, it emits a spectral band of radiation which peaks at 1050 nm

†Specifications

1)Product No.	Infrared LED Lamp	Outer Dimension
2)type No.	L1050-03US	
3)Chip		
(1)Chip material	GaAs	
(2)Peak wavelength	1050 nm	
4)Package		
(1)type	5 mm clear molding	
(2)Resin material	Epoxy resin	
(3)Lead frame	Soldered	



†Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	PD	130	mW	Ta=25 °C
Forward Current	IF	100	mA	Ta=25 °C
Pulse Forward Current	IFP	500	mA	Ta=25 °C
Reverse Voltage	VR	5	V	Ta=25 °C
Operating Temperature	TOPR	-30~+85	°C	
Storage Temperature	TSTG	-30~+100	°C	
Soldering Temperature	TSOL	260	°C	

†Electro-Optical Characteristics (Ta=25 °C)

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50 mA		1.25	1.55	V
Reverse Current	IR	VR=5 V			10	uA
Total Radiation Power	Po	IF=50 mA	1.0	2.5		mW
Radiant Intensity	IE	IF=50 mA	0.7	1.5		mW/Sr
Peak Wavelength	P	IF=50 mA	1000	1050	1100	nm
Half Width	l	IF=50 mA		55		nm
Viewing Half Angle		IF=50 mA		±15°		deg.
Rise Time	Tr	IF=50 mA		10		ns
Fall time	Tf	IF=50 mA		10		ns

‡Brightness is measured by Tektronix J-6512.

‡Total Radiated Power is measured by Photodyne #500.

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